BRB100N03

Rev.A Jul.-2016

DATA SHEET

/ Descriptions

TO-263 N MOS N-CHANNEL MOSFET in a TO-263 Plastic Package.

/ Features

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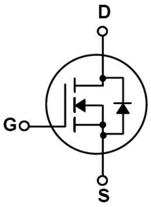
Low gate charge, low crss, fast switching.

/ Applications

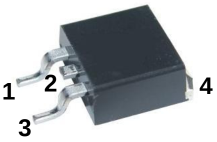
DC/DC

These devices are well suited for high efficiency switching DC/DC converters and switch mode power supplies.

/ Equivalent Circuit



/ Pinning



PIN1 G PIN 2,4 D PIN 3 S

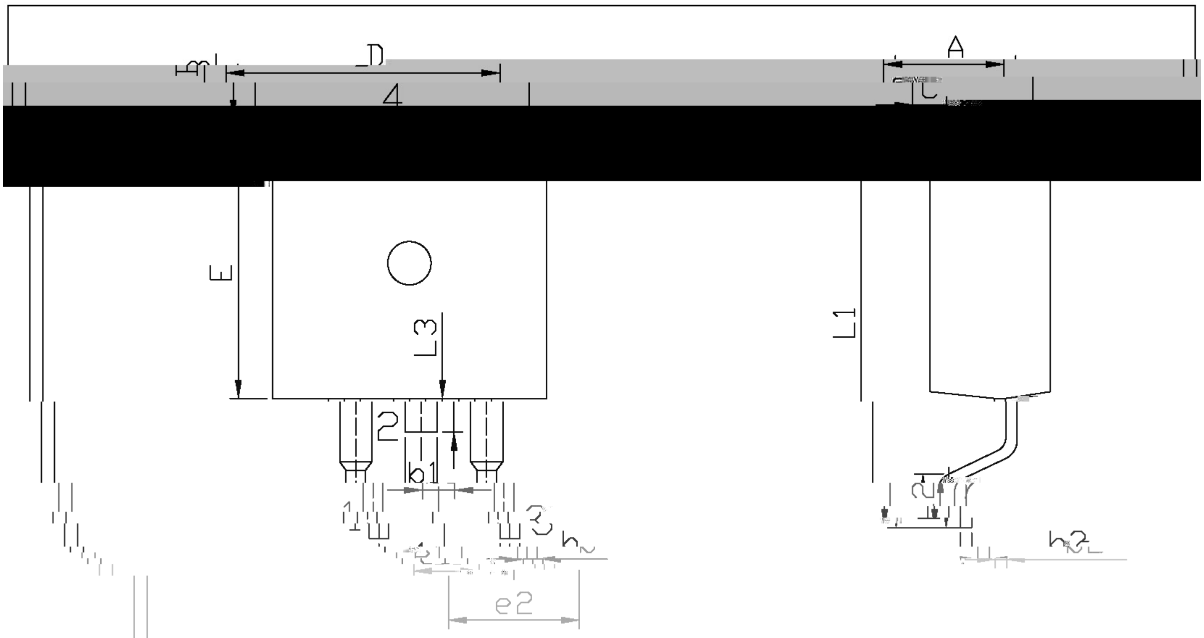
/ h_{FE} Classifications & Marking

See Marking Instructions.

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DSS}	30	V
Drain Current	I_D(Tc=25)	100	A
Peak Drain Current	I_{DM}	400	A
Gate-Source Voltage	V_{GSS}	±20	V
Single Pulsed Avalanche Energy	E_{AS}	875	mJ
Total Power Dissipation	P_D(Tc=25)	100	W
Junction and Storage Temperature Range	T_J,T_{STG}	-55 to 150	

Parameter	Symbol	Test Conditions		Min	Typ	Max	Unit
Zero Gate Voltage Drain Current	BV_{DSS}	V_{GS}=0V	I_D=250μA	30			V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=30V	V_{GS}=0V			1	μA
Gate-Body Leakage Current Forward	I_{GSS}	V_{GS}=±20V	V_{DS}=0V			±0.1	μA
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS}	I_D=250μA	1.0		3.0	V
Forward On Voltage	V_{SD}	I_S=20A	V_{GS}=0V			1.5	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS}=10V	I_D=50A		3.5	4.5	mΩ

/ Package Dimensions



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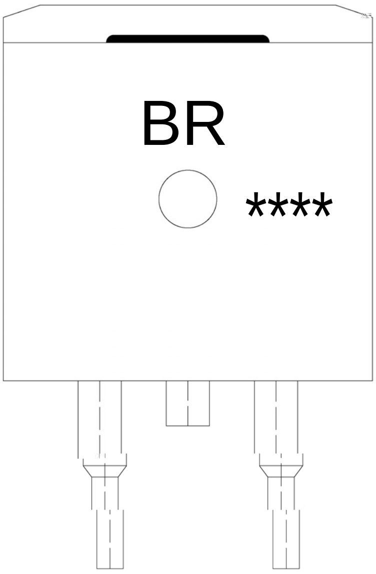
Symbol	Dimensions In Millimeters Min	Max	Symbol	Dimensions In Millimeters Min
A	4.30	4.70	E	9.00
B	1.00	1.40	e1	2.34

/ Marking Instructions



BR

100N03

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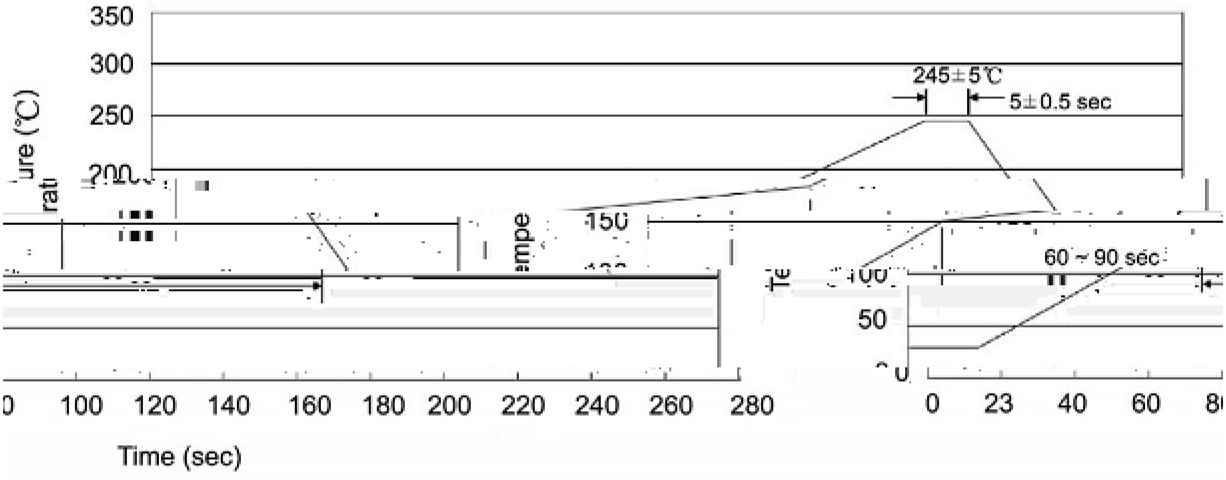
Note:

BR:	Company Code
100N03:	Product Type.
****:	Lot No. Code, code change with Lot No.

( ) / Temperature Profile for Dip Soldering(Pb-Free)



1 25 150 60 90sec;

2 245±5 5±0.5sec;

3 2 10 /sec.

Note:

1.Preheating:25~150 , Time:60~90sec.

2.Peak Temp.:245±5 , Duration:5±0.5sec.

3. Cooling Speed: 2~10 /sec.

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